

L Number	Hits	Search Text	DB	Time stamp
1	366	438/482	USPAT	2003/05/26 12:41
2	197	438/483	USPAT	2003/05/26 12:41
3	312	438/485	USPAT	2003/05/26 12:41
4	504	438/486	USPAT	2003/05/26 12:41
5	413	438/487	USPAT	2003/05/26 12:41
6	488	438/488	USPAT	2003/05/26 12:41
7	173	438/489	USPAT	2003/05/26 12:41
8	129	438/491	USPAT	2003/05/26 12:41
9	99	438/502	USPAT	2003/05/26 12:41
10	238	438/535	USPAT	2003/05/26 12:41
11	811	438/680	USPAT	2003/05/26 12:42
12	363	438/681	USPAT	2003/05/26 12:42
13	551	438/697	USPAT	2003/05/26 12:42
14	135	438/679	USPAT	2003/05/26 12:42
15	280	438/775	USPAT	2003/05/26 12:42
16	125	438/776	USPAT	2003/05/26 12:42
17	894	438/778	USPAT	2003/05/26 12:42
18	270	438/792	USPAT	2003/05/26 12:42
19	713	438/795	USPAT	2003/05/26 12:42
20	118	438/908	USPAT	2003/05/26 12:42
-	0	( single adj crystalline adj nitride adj substrate adj using hydride adj vapor adj phase adj epitaxial adj2 laser adj beam)	USPAT	2003/05/26 11:04
-	0	( single adj crystalline adj nitride adj substrate) and (hydride adj vapor adj phase adj epitaxial) and (laser adj beam) and apparatus and chamber	USPAT	2003/05/26 11:05
-	0	( single adj crystalline adj nitride adj substrate) and laser and apparatus and chamber and beam and temperature and (parent adj substrate)	USPAT	2003/05/26 11:08
-	0	( single adj crystalline adj nitride adj substrate) and laser and apparatus and chamber and beam and temperature	USPAT	2003/05/26 11:08
-	0	( single adj crystalline adj nitride) and laser and apparatus and chamber and beam and temperature and (parent adj substrate)	USPAT	2003/05/26 11:08
-	✓ 2	( single adj crystalline adj nitride) and laser and apparatus and chamber and beam and temperature	USPAT	2003/05/26 11:10
-	1	("6218207").PN.	USPAT	2003/05/26 11:10
-	1	("6358770").PN.	USPAT	2003/05/26 11:10
-	1	("5938839").PN.	USPAT	2003/05/26 11:10
-	1	("4579750").PN.	USPAT	2003/05/26 11:10
-	0	(( single adj crystalline adj nitride adj substrate) and (hydride adj vapor adj phase adj epitaxial) and (laser adj beam) and apparatus and chamber) and (temprature or "600" or "1000" or "1100" or "900" or nitrogen or reacting or substrate or parent or room or backside or nitride or cyrstalline or supporter or heating or annealing or injecting or ammonia or gas or shutters or hydride or vapor or phase or sapphire or spinel or silicon or carbide or epitaxy or epitaxial or hydrochloric or acid )	USPAT	2003/05/26 11:17
-	2	(( single adj crystalline adj nitride) and laser and apparatus and chamber and beam and temperature ) and (temprature or "600" or "1000" or "1100" or "900" or nitrogen or reacting or substrate or parent or room or backside or nitride or cyrstalline or supporter or heating or annealing or injecting or ammonia or gas or shutters or hydride or vapor or phase or sapphire or spinel or silicon or carbide or epitaxy or epitaxial or hydrochloric or acid )	USPAT	2003/05/26 11:47
-	1	(("5938839").PN.) and (temprature or "600" or "1000" or "1100" or "900" or nitrogen or reacting or substrate or parent or room or backside or nitride or cyrstalline or supporter or heating or annealing or injecting or ammonia or gas or shutters or hydride or vapor or phase or sapphire or spinel or silicon or carbide or epitaxy or epitaxial or hydrochloric or acid )	USPAT	2003/05/26 11:55

-	1	(("4579750").PN.) and (temprature or "600" or "1000" or "1100" or "900" or nitrogen or reacting or substrate or parent or room or backside or nitride or cyrstalline or supporter or heating or annealing or injecting or ammonia or gas or shutters or hydride or vapor or phase or sapphire or spinel or silicon or carbide or epitaxy or epitaxial or hydrochloric or acid )	USPAT	2003/05/26 12:40
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5/26/03